



## Versatile RRAM Technology and Applications

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#### Agenda

Overview of RRAM Technology

## RRAM for

- Embedded Memory
- Mass Storage Memory
- Storage Class Memory
- FPGA Configuration, NVRAM, State Retainer
- Monolithic system integration







## Crossbar's RRAM Technology

- Simple device structure using fab friendly materials and process
- Information is stored in the form of metallic nano-filament in a non-conductive layer
- Filamentary-based switching by electric field







## Crossbar Technology





Suited for low latency, high speed embedded memory

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#### Crossbar Selector







Suited for high density high performance NAND or SCM memory





## Scaling Improves Crossbar RRAM



#### Scaling RRAM device

- Roff increases by  $\frac{1}{Cell Area}$
- Ron Stays nearly constant
- Roff/Ron ratio improves
- Sensing window improves
- Improves BER
- Provides additional margin for MLC/TLC





## Benefits of Crossbar Embedded RRAM



No Change to Front-end

- Major changes to Front-end
  - Complex cell
  - High voltage transistors
- Adds 6+ Masks & 40 steps





## Benefits of Crossbar Embedded RRAM



- Back-end process minimum impact
- RRAM located between metal layers
- Adds only 2 masks & 8 steps
- 32% lower cost
- Smaller die size





## Advantages of RRAM for Embedded Memory

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Scales with advanced nodes	Reduced Manufacturing Complexity	Cost	Performance
	<ul> <li>CMOS compatible material</li> <li>Back-end process - No change in front-end</li> </ul>	<ul> <li>Reduced masking steps</li> </ul>	<ul> <li>Byte/Page Alterability</li> <li>Write operation – no need for block erase</li> </ul>





## **RRAM for Mass Storage**

& retention

#### Performance

- Latency reduction
- Byte/Page alterability
- Smaller page sizes
- Write no need for block erase

#### Density and Scalability

 3D crosspoint array stackable at advanced nodes

#### Utilizes standard CMOS process

**Superior endurance** 

 Mass storage available to Fabless companies









#### Crossbar Memory Byte/Page Alterability Demonstration







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## **Crossbar Patented IP Libraries**

#### **FPGA** Configuration Bit



- Instant On
- Eliminates external non-volatile memory

#### **NVRAM**



#### **State Retainer**



- Stores data at power down
- Recalls at power up
- Power saving





# RRAM for FPGA Configuration Bits, NVRAM, State Retainer

- Major Advantages:
  - NV Configuration bit
  - Area reduction
  - Performance improvement
  - Power reduction
  - Instant on
    - No need for external non-volatile memory
  - Embedded non-volatile memory for data/code/storage



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## **RRAM for Monolithic Integration**



- Elimination of large number of I/Os, and simplification of the external interface
  - Reduction of components
  - Power reduction due to elimination of large number of I/O
- Breakthrough performance
  - Direct wide bus connection between memory and CPU/peripheral devices

#### **Crossbar technology = True high performance integrated system**

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## Monolithic Integration of NVMemory with **Crossbar RRAM**

Crossbar RRAM Technology Enables Monolithic integration of:





Crossbar Unique RRAM Versatile Technology

- Monolithic integration of Storage, Code, Data, FPGA configuration bit memories in one silicon
- Breakthrough system performance enabled with the monolithic integration of various memory architectures
- Fabless companies access IPs for a complete memory solution (storage, code, data, and FPGA configuration) from CMOS foundries







## Ready for Business

#### Crossbar RRAM 300mm Wafer



Crossbar RRAM Die





#### Crossbar-inc.com

